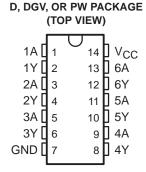
- EPIC™ (Enhanced-Performance Implanted CMOS) Submicron Process
- ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 250 mA Per JESD 17
- Package Options Include Plastic Small-Outline (D), Thin Very Small-Outline (DGV), and Thin Shrink Small-Outline (PW) Packages



description

This hex inverter contains six independent inverters designed for 1.65-V to 3.6-V V_{CC} operation.

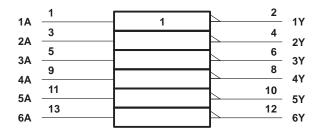
The SN74ALVC04 performs the Boolean function $Y = \overline{A}$.

The SN74ALVC04 is characterized for operation from -40°C to 85°C.

FUNCTION TABLE (each inverter)

INPUT A	OUTPUT Y
Н	L
L	Н

logic symbol†



[†] This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram, each inverter (positive logic)





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absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V _{CC}	
Input voltage range, V _I (see Note 1)	
Output voltage range, VO (see Notes 1 and 2)	0.5 V to V _{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$)	
Output clamp current, I _{OK} (V _O < 0)	–50 mA
Continuous output current, IO	±50 mA
Continuous current through V _{CC} or GND	±100 mA
Package thermal impedance, θ _{JA} (see Note 3): D packa	ge 127°C/W
DGV pa	ckage 182°C/W
PW pac	kage 170°C/W
Storage temperature range, T _{stg}	

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES: 1. The input negative-voltage and output voltage ratings may be exceeded if the input and output current ratings are observed.
 - 2. This value is limited to 4.6 V maximum.
 - 3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT	
Vcc	Supply voltage		1.65	3.6	V	
		V _{CC} = 1.65 V to 1.95 V	0.65 × V _{CC}			
V_{IH}	High-level input voltage	$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	1.7		V	
		$V_{CC} = 2.7 \text{ V to } 3.6 \text{ V}$	2			
	Low-level input voltage	V _{CC} = 1.65 V to 1.95 V		$0.35 \times V_{CC}$		
V_{IL}		V _{CC} = 2.3 V to 2.7 V		0.7	V	
		$V_{CC} = 2.7 \text{ V to } 3.6 \text{ V}$		0.8	1	
٧ _I	Input voltage	0	Vcc	V		
٧o	Output voltage		0	Vcc	V	
	High-level output current	V _{CC} = 1.65 V		-4		
1		V _{CC} = 2.3 V		-12	mA	
ЮН		V _{CC} = 2.7 V		-12		
		V _{CC} = 3 V		-24		
		V _{CC} = 1.65 V		4		
lOL	Low-level output current	V _{CC} = 2.3 V		12	mA	
		V _{CC} = 2.7 V		12		
		V _{CC} = 3 V		24		
Δt/Δν	Input transition rise or fall rate	-		5	ns/V	
TA	Operating free-air temperature		-40	85	°C	

NOTE 4: All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, literature number SCBA004.



electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CO	ONDITIONS	vcc	MIN	TYP [†]	MAX	UNIT
	I _{OH} = -100 μA		1.65 V to 3.6 V	V _{CC} -0.	2		
	$I_{OH} = -4 \text{ mA}$		1.65 V	1.2			
	$I_{OH} = -6 \text{ mA}$		2.3 V	2			
Voн			2.3 V	1.7			V
	$I_{OH} = -12 \text{ mA}$		2.7 V	2.2			
			3 V	2.4			
	I _{OH} = -24 mA		3 V	2			
	I _{OL} = 100 μA		1.65 V to 3.6 V			0.2	
	$I_{OL} = 4 \text{ mA}$		1.65 V			0.45	
VOL	$I_{OL} = 6 \text{ mA}$		2.3 V			0.4	٧
VOL	I _{OL} = 12 mA		2.3 V			0.7	V
	IOL = 12 IIIA		2.7 V			0.4	
	$I_{OL} = 24 \text{ mA}$		3 V			0.55	
ΙĮ	$V_I = V_{CC}$ or GND		3.6 V			±5	μΑ
ICC	$V_I = V_{CC}$ or GND,	IO = 0	3.6 V			10	μΑ
ΔlCC	One input at V _{CC} – 0.6 V,	Other inputs at V _{CC} or GND	3 V to 3.6 V			750	μΑ
C _i	$V_I = V_{CC}$ or GND		3.3 V		3.5	·	pF

[†] All typical values are at $V_{CC} = 3.3 \text{ V}$, $T_A = 25^{\circ}\text{C}$.

switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 through 3)

PARAMETER	R FROM TO (OUTPUT)	V _{CC} = 1.8 V	V _{CC} = 2.5 V ± 0.2 V		V _{CC} = 2.7 V		V _{CC} = 3.3 V ± 0.3 V		UNIT	
		(0011 01)	TYP	MIN	MAX	MIN	MAX	MIN	MAX	
^t pd	А	Υ	‡	1	3		3.3	1	2.8	ns

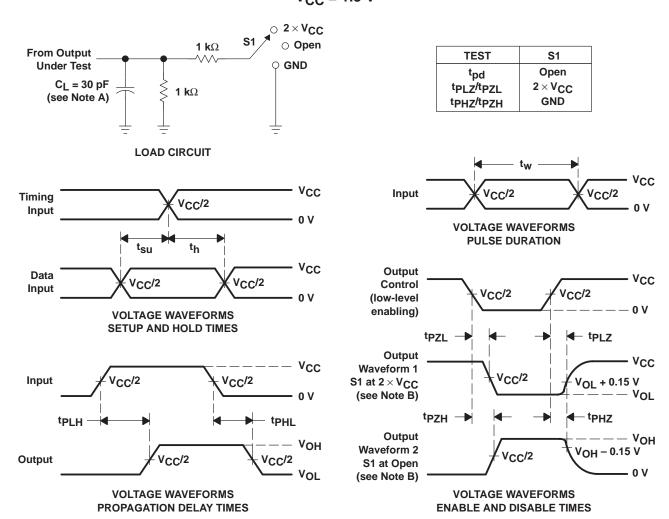
[‡] This information was not available at the time of publication.

operating characteristics, T_A = 25°C

PARAMETER		TEST CONDITIONS	V _{CC} = 1.8 V	V _{CC} = 2.5 V	V _{CC} = 3.3 V	UNIT
		TEST CONDITIONS	TYP	TYP	TYP	UNIT
C _{pd}	Power dissipation capacitance per inverter	$C_L = 0$, $f = 10 \text{ MHz}$	‡	23	27.5	pF

[‡] This information was not available at the time of publication.

PARAMETER MEASUREMENT INFORMATION V_{CC} = 1.8 V



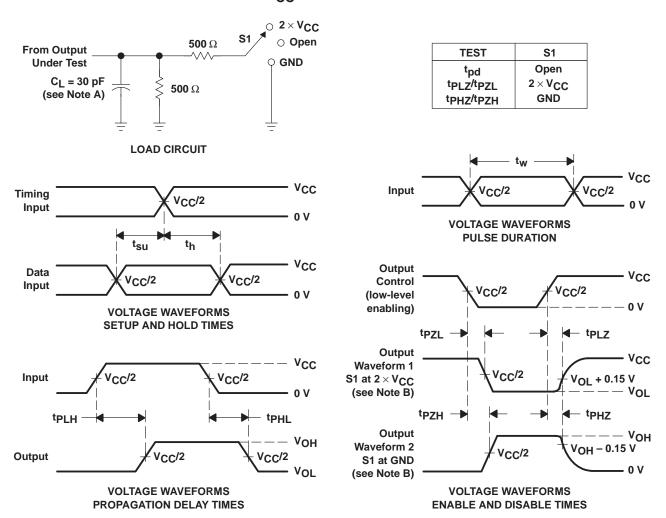
NOTES: A. CL includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_O = 50~\Omega$, $t_f \leq$ 2 ns, $t_f \leq$ 2 ns.
- D. The outputs are measured one at a time with one transition per measurement.
- E. tpLz and tpHz are the same as tdis.
- F. tpzL and tpzH are the same as ten.
- G. tpLH and tpHL are the same as tpd.

Figure 1. Load Circuit and Voltage Waveforms



PARAMETER MEASUREMENT INFORMATION $V_{CC} = 2.5 \text{ V} \pm 0.2 \text{ V}$

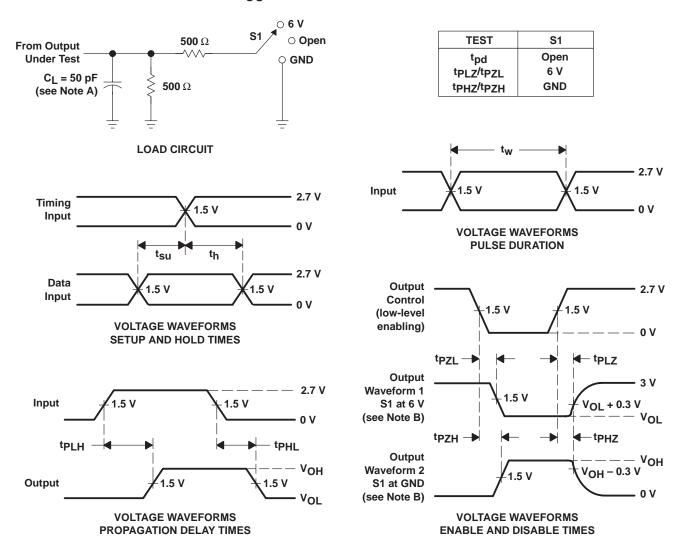


NOTES: A. C_L includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_O = 50~\Omega$, $t_f \leq$ 2 ns. $t_f \leq$ 2 ns.
- D. The outputs are measured one at a time with one transition per measurement.
- E. tpLz and tpHz are the same as tdis.
- F. tpzL and tpzH are the same as ten.
- G. tpLH and tpHL are the same as tpd.

Figure 2. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION $V_{CC} = 2.7 \text{ V}$ AND 3.3 V \pm 0.3 V



NOTES: A. C_L includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_Q = 50 \Omega$, $t_f \leq 2.5 \text{ ns.}$
- D. The outputs are measured one at a time with one transition per measurement.
- E. tpLz and tpHz are the same as tdis.
- F. tpzL and tpzH are the same as ten.
- G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 3. Load Circuit and Voltage Waveforms



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